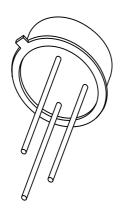
### **DISCRETE SEMICONDUCTORS**

# DATA SHEET



## BC107; BC108; BC109 NPN general purpose transistors

Product specification Supersedes data of 1997 Jun 03 File under Discrete Semiconductors, SC04 1997 Sep 03





### NPN general purpose transistors

BC107; BC108; BC109

#### **FEATURES**

- Low current (max. 100 mA)
- Low voltage (max. 45 V).

#### **APPLICATIONS**

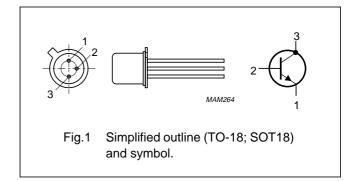
• General purpose switching and amplification.

#### **DESCRIPTION**

NPN transistor in a TO-18; SOT18 metal package. PNP complement: BC177.

#### **PINNING**

PIN	DESCRIPTION
1	emitter
2	base
3	collector, connected to the case



#### **QUICK REFERENCE DATA**

SYMBOL	PARAMETER	CONDITIONS	MIN.	MAX.	UNIT
V <sub>CBO</sub>	collector-base voltage	open emitter			
	BC107		_	50	V
	BC108; BC109		_	30	V
V <sub>CEO</sub>	collector-emitter voltage	open base			
	BC107		_	45	V
	BC108; BC109		_	20	V
I <sub>CM</sub>	peak collector current		_	200	mA
P <sub>tot</sub>	total power dissipation	T <sub>amb</sub> ≤ 25 °C	_	300	mW
h <sub>FE</sub>	DC current gain	I <sub>C</sub> = 2 mA; V <sub>CE</sub> = 5 V			
	BC107		110	450	
	BC108		110	800	
	BC109		200	800	
f <sub>T</sub>	transition frequency	I <sub>C</sub> = 10 mA; V <sub>CE</sub> = 5 V; f = 100 MHz	100	_	MHz

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#### **LIMITING VALUES**

In accordance with the Absolute Maximum Rating System (IEC 134).

SYMBOL	PARAMETER	CONDITIONS	MIN.	MAX.	UNIT
V <sub>CBO</sub>	collector-base voltage	open emitter			
	BC107		_	50	V
	BC108; BC109		_	30	V
V <sub>CEO</sub>	collector-emitter voltage	open base			
	BC107		_	45	V
	BC108; BC109		_	20	V
V <sub>EBO</sub>	emitter-base voltage	open collector			
	BC107		_	6	V
	BC108; BC109		_	5	V
I <sub>C</sub>	collector current (DC)		_	100	mA
I <sub>CM</sub>	peak collector current		_	200	mA
I <sub>BM</sub>	peak base current		_	200	mA
P <sub>tot</sub>	total power dissipation	T <sub>amb</sub> ≤ 25 °C	_	300	mW
T <sub>stg</sub>	storage temperature		-65	+150	°C
Tj	junction temperature			175	°C
T <sub>amb</sub>	operating ambient temperature		-65	+150	°C

#### THERMAL CHARACTERISTICS

SYMBOL	PARAMETER	CONDITIONS	VALUE	UNIT
R <sub>th j-a</sub>	thermal resistance from junction to ambient	note 1	0.5	K/mW
R <sub>th j-c</sub>	thermal resistance from junction to case		0.2	K/mW

#### Note

1. Transistor mounted on an FR4 printed-circuit board.

### NPN general purpose transistors

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#### **CHARACTERISTICS**

 $T_j = 25$  °C unless otherwise specified.

SYMBOL	PARAMETER	CONDITIONS	MIN.	TYP.	MAX.	UNIT
I <sub>CBO</sub>	collector cut-off current	I <sub>E</sub> = 0; V <sub>CB</sub> = 20 V	_	_	15	nA
		I <sub>E</sub> = 0; V <sub>CB</sub> = 20 V; T <sub>j</sub> = 150 °C	_	_	15	μΑ
I <sub>EBO</sub>	emitter cut-off current	I <sub>C</sub> = 0; V <sub>EB</sub> = 5 V	_	_	50	nA
h <sub>FE</sub>	DC current gain	$I_C = 10 \mu\text{A};  V_{CE} = 5  \text{V}$				
	BC107A; BC108A		_	90	_	
	BC107B; BC108B; BC109B		40	150	_	
	BC108C; BC109C		100	270	_	
h <sub>FE</sub>	DC current gain	I <sub>C</sub> = 2 mA; V <sub>CE</sub> = 5 V				
	BC107A; BC108A		110	180	220	
	BC107B; BC108B; BC109B		200	290	450	
	BC108C; BC109C		420	520	800	
V <sub>CEsat</sub>	collector-emitter saturation voltage	I <sub>C</sub> = 10 mA; I <sub>B</sub> = 0.5 mA	_	90	250	mV
		I <sub>C</sub> = 100 mA; I <sub>B</sub> = 5 mA	_	200	600	mV
V <sub>BEsat</sub>	base-emitter saturation voltage	$I_C = 10 \text{ mA}; I_B = 0.5 \text{ mA}; \text{ note 1}$	_	700	_	mV
	!	I <sub>C</sub> = 100 mA; I <sub>B</sub> = 5 mA; note 1	_	900	_	mV
V <sub>BE</sub>	base-emitter voltage	I <sub>C</sub> = 2 mA; V <sub>CE</sub> = 5 V; note 2	550	620	700	mV
		I <sub>C</sub> = 10 mA; V <sub>CE</sub> = 5 V; note 2	_	_	770	mV
C <sub>c</sub>	collector capacitance	$I_E = i_e = 0$ ; $V_{CB} = 10 \text{ V}$ ; $f = 1 \text{ MHz}$	_	2.5	6	pF
C <sub>e</sub>	emitter capacitance	$I_C = i_c = 0$ ; $V_{EB} = 0.5 \text{ V}$ ; $f = 1 \text{ MHz}$	_	9	_	pF
f <sub>T</sub>	transition frequency	$I_C = 10 \text{ mA}; V_{CB} = 5 \text{ V}; f = 100 \text{ MHz}$	100	_	_	MHz
F	noise figure	$I_C = 200 \mu A; V_{CE} = 5 V; R_S = 2 k\Omega;$				
	BC109B; BC109C	f = 30 Hz to 15.7 kHz	_	_	4	dB
F	noise figure	$I_C = 200 \mu A; V_{CE} = 5 V; R_S = 2 k\Omega;$				
	BC107A; BC108A	f = 1 kHz; B = 200 Hz	_	_	10	dB
	BC107B; BC108B; BC108C					
	BC109B; BC109C		_	_	4	dB

#### Notes

- 1.  $V_{BEsat}$  decreases by about 1.7 mV/K with increasing temperature.
- 2.  $V_{BE}$  decreases by about 2 mV/K with increasing temperature.

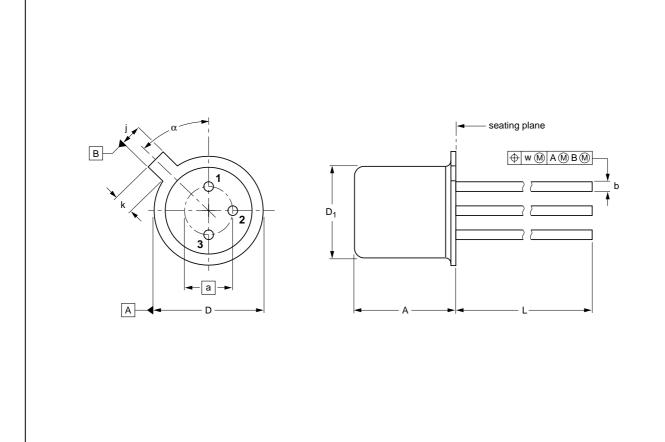
### NPN general purpose transistors

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#### **PACKAGE OUTLINE**

Metal-can cylindrical single-ended package; 3 leads

SOT18/13



#### DIMENSIONS (millimetre dimensions are derived from the original inch dimensions)

UNIT	A	а	b	D	D <sub>1</sub>	j	k	L	w	α
mm	5.31 4.74	2.54	0.47 0.41	5.45 5.30		1.03 0.94	1.1 0.9	15.0 12.7	0.40	45°

OUTLINE	REFERENCES		REFERENCES			EUROPEAN	ISSUE DATE
VERSION	IEC	JEDEC	EIAJ	PROJECTION	ISSUE DATE		
SOT18/13	B11/C7 type 3	TO-18			97-04-18		

Product specification Philips Semiconductors

### NPN general purpose transistors

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#### **DEFINITIONS**

Data Sheet Status	
Objective specification	This data sheet contains target or goal specifications for product development.
Preliminary specification	This data sheet contains preliminary data; supplementary data may be published later.
Product specification	This data sheet contains final product specifications.
Limiting values	

Limiting values given are in accordance with the Absolute Maximum Rating System (IEC 134). Stress above one or more of the limiting values may cause permanent damage to the device. These are stress ratings only and operation of the device at these or at any other conditions above those given in the Characteristics sections of the specification is not implied. Exposure to limiting values for extended periods may affect device reliability.

#### **Application information**

Where application information is given, it is advisory and does not form part of the specification.

#### LIFE SUPPORT APPLICATIONS

These products are not designed for use in life support appliances, devices, or systems where malfunction of these products can reasonably be expected to result in personal injury. Philips customers using or selling these products for use in such applications do so at their own risk and agree to fully indemnify Philips for any damages resulting from such improper use or sale.

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## NPN general purpose transistors

BC107; BC108; BC109

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